

1 93. The device of claim 76, wherein said plurality of layers of semiconductor material with
2 different optical indices are made in the $Al_xGa_yIn_{1-x-y}N$ semiconductor system on a SiC
3 substrate.

1 94. The device of claim 76, wherein said plurality of layers of semiconductor material with
2 different optical indices are made in a the $Al_xGa_yIn_{1-x-y}As_zN_{1-z}$ semiconductor systems on a
3 GaAs substrate.

1 95. The device of claim 76 wherein said plurality of layers of semiconductor material with
2 different optical indices are made of II-VI compound semiconductors.

1 96. The device of claim 76 wherein said plurality of layers of semiconductor material with
2 different optical indices are made of IV-VI compound semiconductors.

RESPONSE

In response to the Restriction Requirement of November 5, 2002, Applicant elects species 12, drawn to claims 13-18 and 20-27. These claims are generic because they read upon all the alleged species. Furthermore, claims 56-96 are also generic because they also read upon all the alleged species.

end

Examination on the merits is respectfully requested.

Respectfully submitted,



Matthew E. Connors
Registration No. 33,298
Samuels, Gauthier & Stevens
225 Franklin Street
Boston, Massachusetts 02110
Telephone: (617) 426-9180
Extension: 112